

ABSTRACT OF THE DISCLOSURE

A method for forming a junction in a semiconductor device including the steps of: forming a photoresist film pattern on a semiconductor substrate
5 excluding a halo implant region; performing a first halo implant process on the halo implant region of the semiconductor substrate by using a tilt angle of about 45°; and performing a second halo implant process on the halo implant region of the semiconductor substrate
10 by using a tilt angle of about 0°.